TPD-8D12-673

Non-hermetic 25Gbps GaAs PIN photodiode chip

FEATURES:

- High responsivity at 850nm.
- Optimized for fiber optic application.
- Low dark current and low capacitance.
- Planarized and Non-hermetic design.

ELECTRO-OPTICAL CHARACTERISTICS: (T=25℃)

PARAMETERS	SYMBOL	MIN	TYP	MAX	UNIT	TEST CONDITIONS
Responsivity	R	0.55	0.6		A/W	V_R=2V, λ=850nm
Dark Current	I_D		0.1	1	nA	V_R=5V
Breakdown Voltage	V_{BD}	30			V	I_R=10μA
Capacitance	C		0.1	0.12	pF	V_R=2V, f=1 MHz
Bandwidth	BW		17		GHz	V_R=2V

ABSOLUTE MAXIMUM RATINGS:

PARAMETERS	MIN	MAX	UNIT	TEST CONDITIONS
Storage Temperature	-40	100	℃	
Operating Temperature	-40	85	℃	
Reverse Current		2	mA	T=25℃
Reverse Voltage		20	V	T=25℃
Forward Current		10	mA	T=25℃

Fig.1 Typical Dark Current and Forward Current

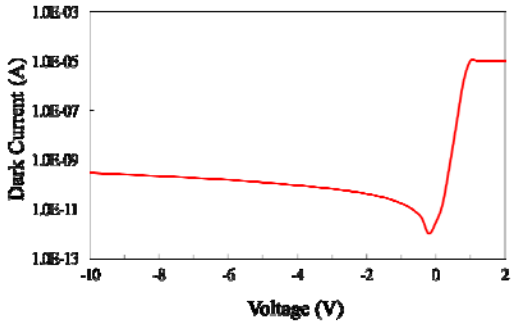

Fig.2 Typical Photo Current

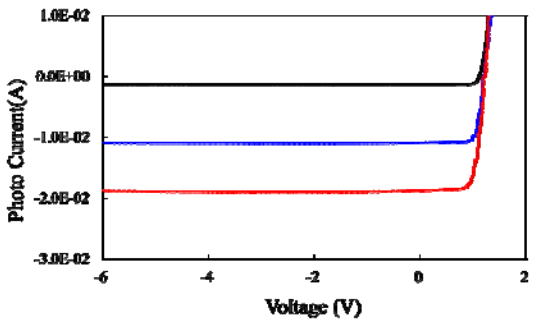

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Fig. 3 Typical Breakdown Curve

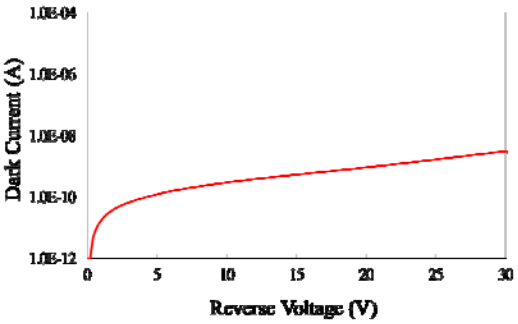
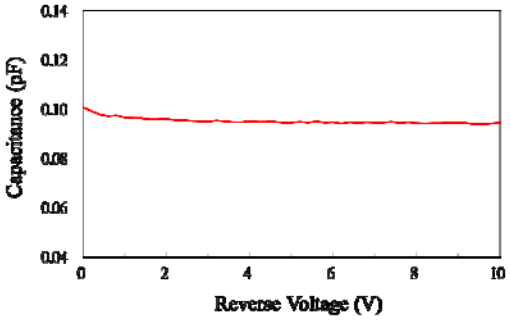
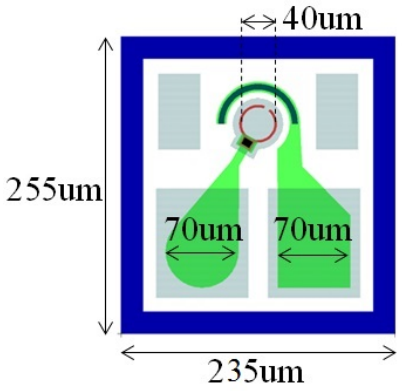


Fig. 4 Typical C-V Curve



OUTLINE DIAGRAM:



- Chip size is typical 235um × 255um.
- Chip thickness is 150±12.5um
- Sensitive area is typical 40um in diameter.

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